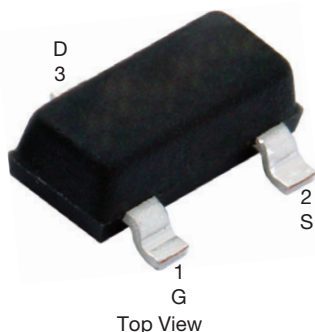


N-Channel 60 V (D-S) MOSFET

SOT-23 (TO-236)



Marking code: 7K

PRODUCT SUMMARY

V_{DS} (V)	60
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10$ V	2
Q_g typ. (nC)	0.4
I_D (A)	0.3
Configuration	Single

FEATURES

- Low on-resistance: $2\ \Omega$
- Low threshold: 2 V (typ.)
- Low input capacitance: 25 pF
- Fast switching speed: 25 ns
- Low input and output leakage
- TrenchFET® power MOSFET
- 2000 V ESD protection
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details



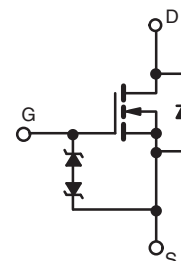
RoHS*
Available
HALOGEN
FREE
Available

BENEFITS

- Low offset voltage
- Low voltage operation
- Easily driven without buffer
- High speed circuits
- Low error voltage

APPLICATIONS

- Direct logic-level interface: TTL/CMOS
- Drivers:
relays, solenoids, lamps, hammers,
display, memories, transistors, etc.
- Battery operated systems
- Solid state relays



N-Channel MOSFET

ORDERING INFORMATION

Package	SOT-23
Lead (Pb)-free	2N7002K-T1-E3
Lead (Pb)-free and halogen-free	2N7002K-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\ ^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	60	V
Gate-source voltage	V_{GS}	± 20	
Continuous drain current ($T_J = 150\ ^\circ\text{C}$) ^b	I_D	0.3	A
		0.19	
Pulsed drain current ^a	I_{DM}	0.8	
Power dissipation ^b	P_D	0.35	W
		0.14	
Maximum junction-to-ambient ^b	R_{thJA}	350	$^\circ\text{C/W}$
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Notes

- a. Pulse width limited by maximum junction temperature
b. Surface mounted on FR4 board



SPECIFICATIONS (T _A = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP. ^a	MAX.	UNIT
Static						
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 10 μA	60	-	-	V
Gate-threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1	-	2.5	
Gate-body leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	± 10	μA
		V _{DS} = 0 V, V _{GS} = ± 15 V	-	-	1	
		V _{DS} = 0 V, V _{GS} = ± 10 V	-	-	± 150	nA
		V _{DS} = 0 V, V _{GS} = ± 10 V, T _J = 85 °C	-	-	± 1000	
		V _{DS} = 0 V, V _{GS} = ± 5 V	-	-	± 100	
Zero gate voltage drain current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V	-	-	1	μA
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C	-	-	500	
On-state drain current ^b	I _{D(on)}	V _{GS} = 10 V, V _{DS} = 7.5 V	800	-	-	mA
		V _{GS} = 4.5 V, V _{DS} = 10 V	500	-	-	
Drain-source on-resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 500 mA	-	-	2	Ω
		V _{GS} = 4.5 V, I _D = 200 mA	-	-	4	
Forward transconductance ^b	g _{fs}	V _{DS} = 10 V, I _D = 200 mA	100	-	-	mS
Diode forward voltage	V _{SD}	I _S = 200 mA, V _{GS} = 0 V	-	-	1.3	V
Dynamic ^{a, b}						
Total gate charge	Q _g	V _{DS} = 10 V, V _{GS} = 4.5 V I _D ≅ 250 mA	-	0.4	0.6	nC
Input capacitance	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V f = 1 MHz	-	30	-	pF
Output capacitance	C _{oss}		-	6	-	
Reverse transfer capacitance	C _{rss}		-	2.5	-	
Switching ^{a, c}						
Turn-on time	t _{d(on)}	V _{DD} = 30 V, R _L = 150 Ω I _D ≅ 200 mA, V _{GEN} = 10 V, R _g = 10 Ω	-	-	25	ns
Turn-off time	t _{d(off)}		-	-	35	

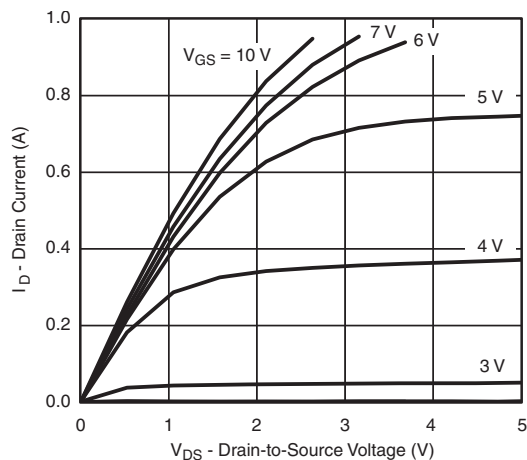
Notes

- a. For DESIGN AID ONLY, not subject to production testing
b. Pulse test: pulse width $\leq 300\text{ }\mu\text{s}$ duty cycle $\leq 2\%$
c. Switching time is essentially independent of operating temperature

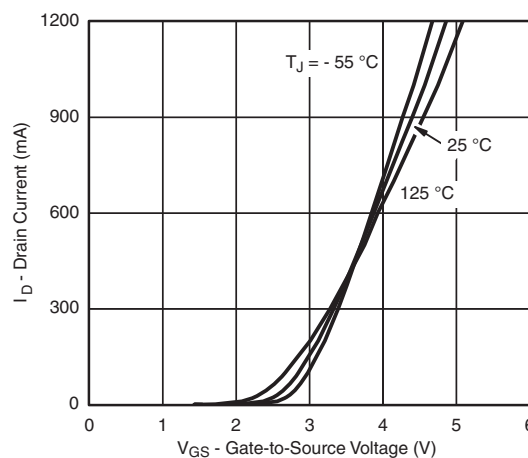
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



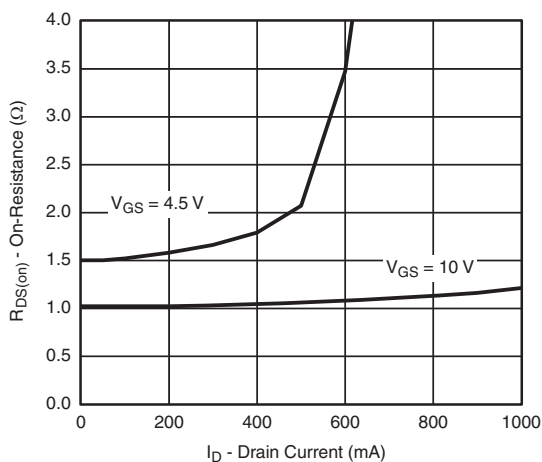
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



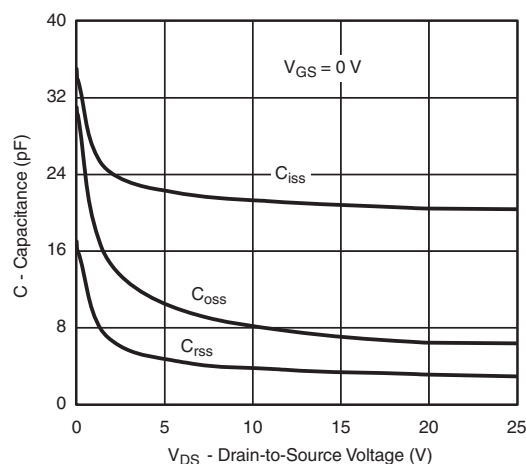
Output Characteristics



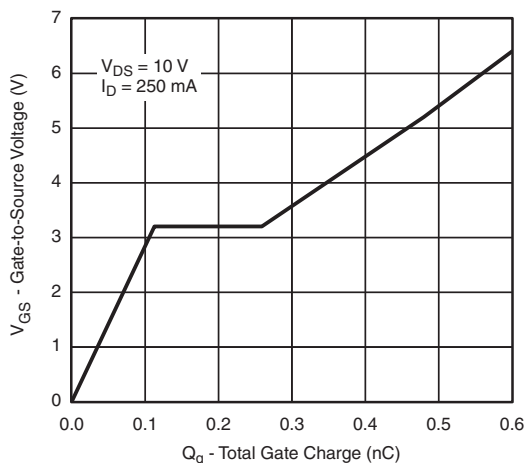
Transfer Characteristics



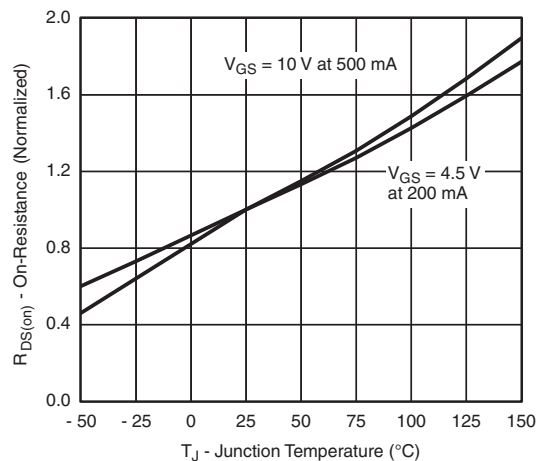
On-Resistance vs. Drain Current



Capacitance



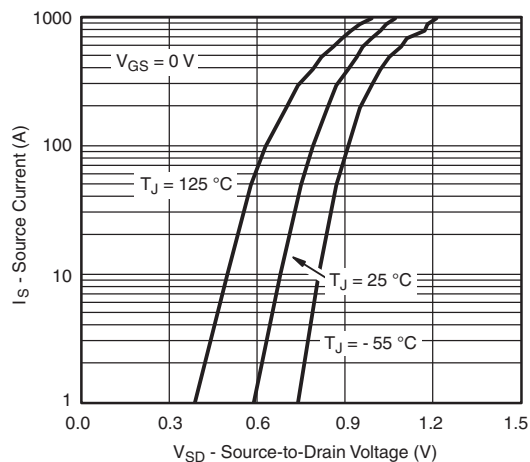
Gate Charge



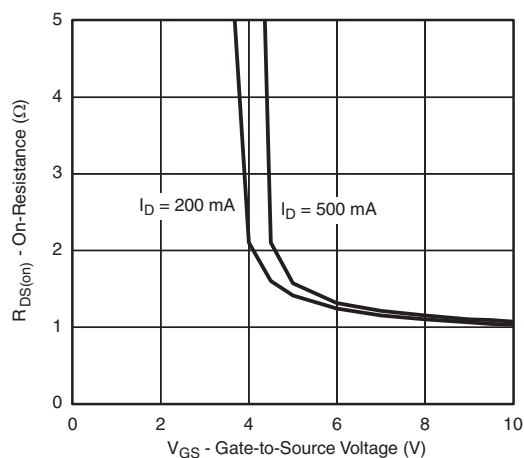
On-Resistance vs. Junction Temperature



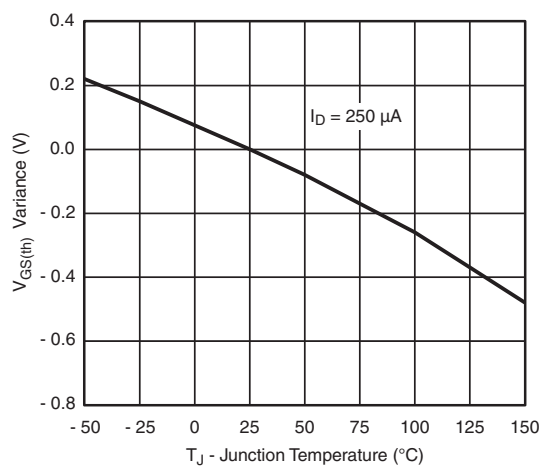
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



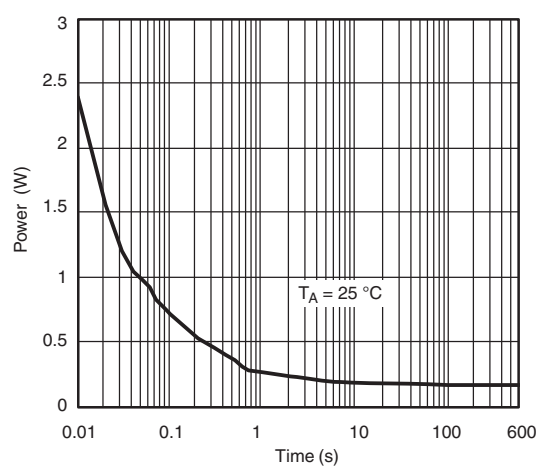
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-Source Voltage



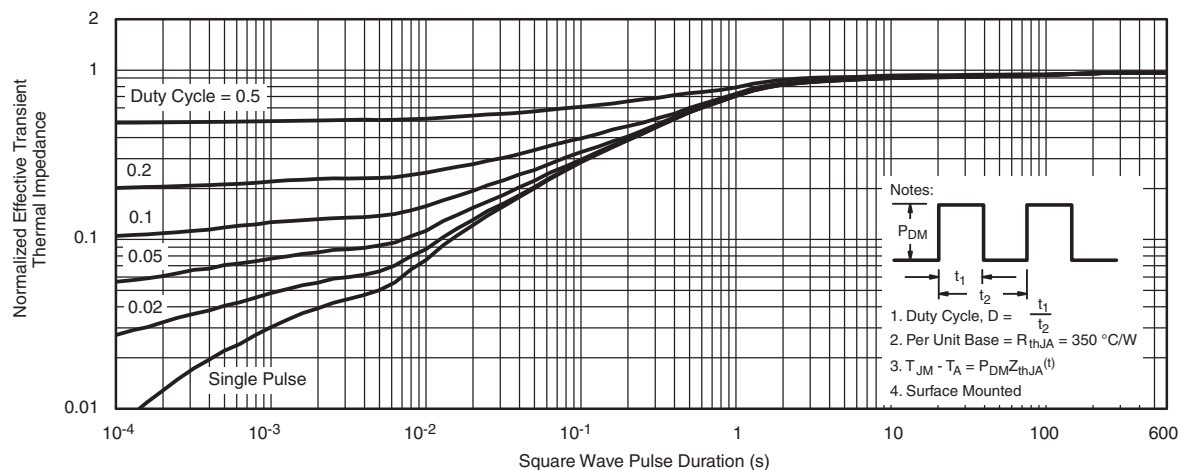
Threshold Voltage Variance Over Temperature



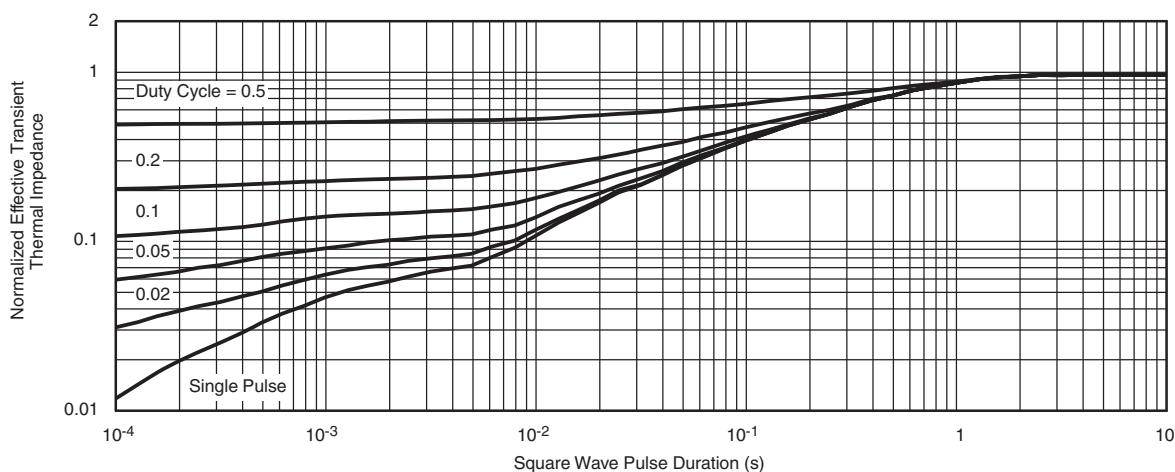
Single Pulse Power, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



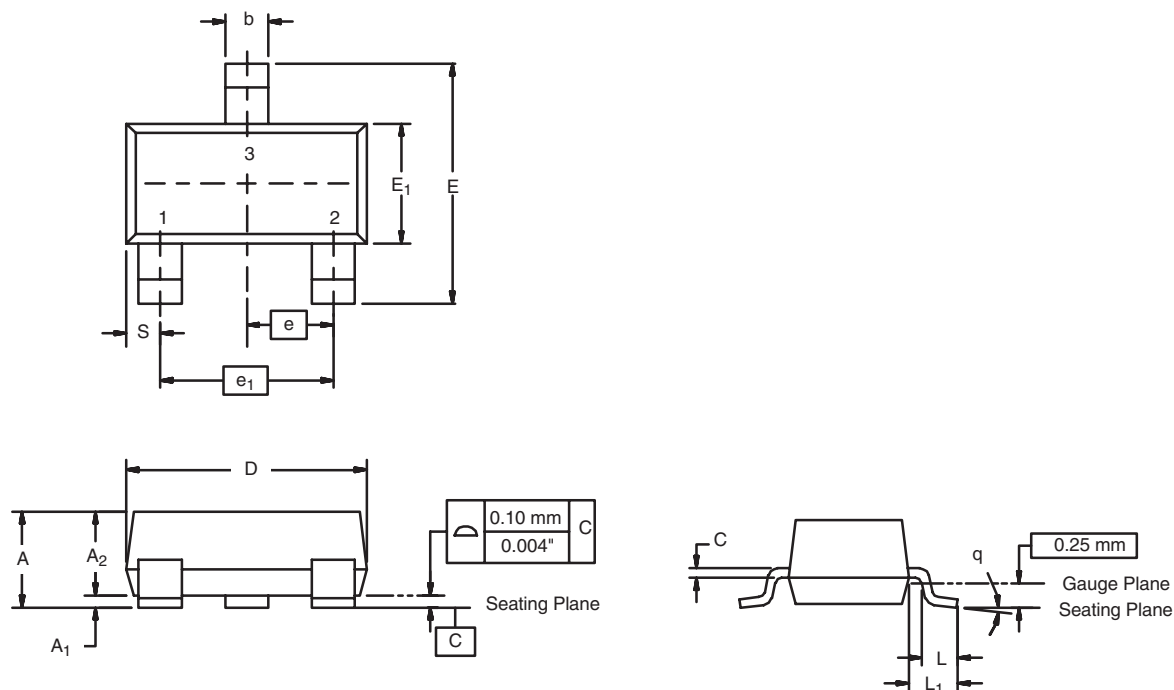
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

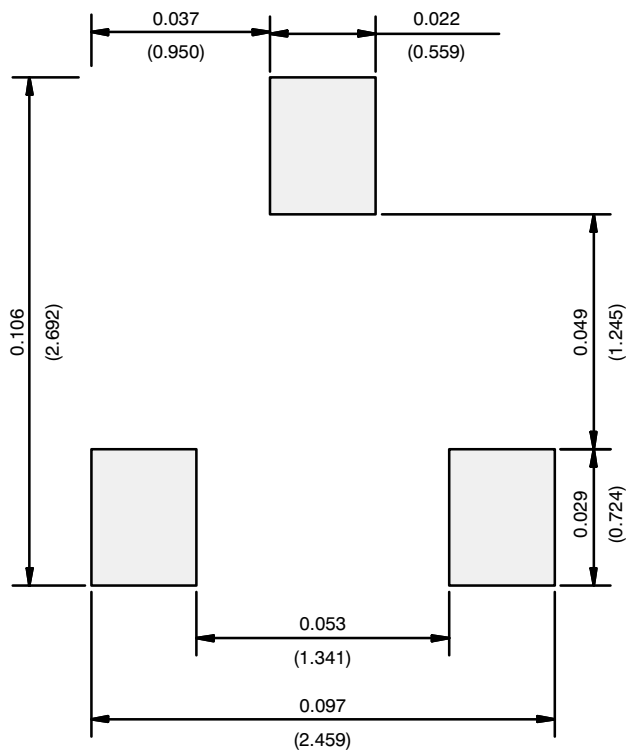
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SOT-23 (TO-236): 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A ₁	0.01	0.10	0.0004	0.004
A ₂	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E ₁	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e ₁	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L ₁	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°
ECN: S-03946-Rev. K, 09-Jul-01				
DWG: 5479				

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads
Dimensions in Inches/(mm)

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